

Dual P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 20	0.019 at $V_{GS} = -10$ V	- 8.4
	0.031 at $V_{GS} = -4.5$ V	- 6.7

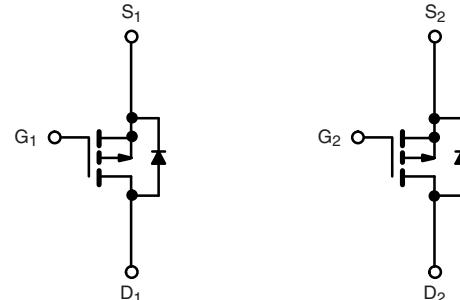
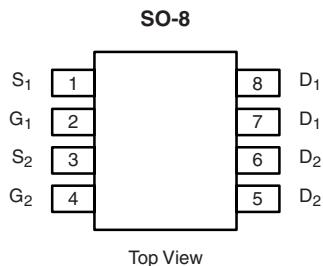
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Load Switching
 - Computer
 - Game Systems
- Battery Switching
 - 2-Cell Li-Ion



Ordering Information: Si4943BDY-T1-E3 (Lead (Pb)-free)
Si4943BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V_{DS}	- 20		V
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D ($T_A = 25$ °C)	- 8.4	- 6.3	A
	I_D ($T_A = 70$ °C)	- 6.7	- 5.1	
Pulsed Drain Current	I_{DM}	- 30		
Continuous Source Current (Diode Conduction) ^a	I_S	- 1.7	- 0.9	
Maximum Power Dissipation ^a	P_D ($T_A = 25$ °C)	2.0	1.1	W
	P_D ($T_A = 70$ °C)	1.3	0.7	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ s	R_{thJA}	46	62.5
	Steady State		85	110
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	26	35

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

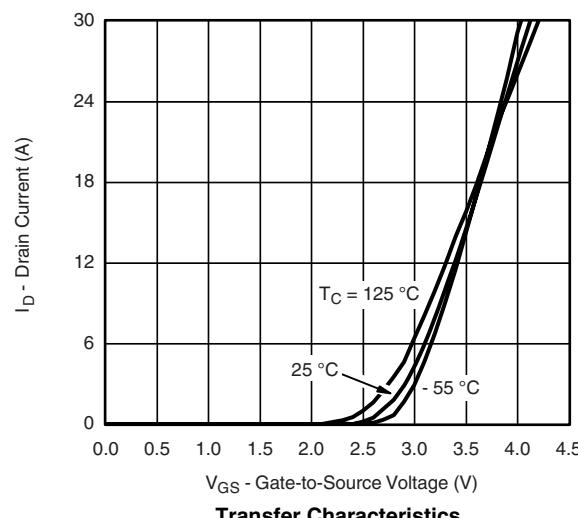
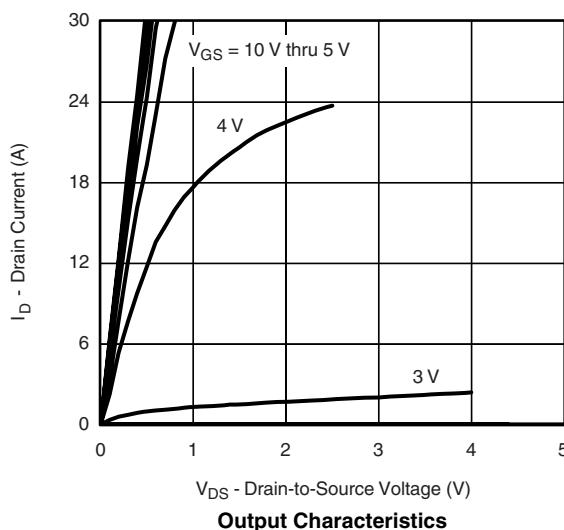
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = -250\ \mu\text{A}$	- 1		- 3	V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 20\ \text{V}$			± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\ \text{V}$, $V_{GS} = 0\ \text{V}$			- 1	μA	
		$V_{DS} = -20\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 55^\circ\text{C}$			- 5		
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} = -5\ \text{V}$, $V_{GS} = -10\ \text{V}$	- 30			A	
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = -10\ \text{V}$, $I_D = -8.4\ \text{A}$		0.016	0.019	Ω	
		$V_{GS} = -4.5\ \text{V}$, $I_D = -6.7\ \text{A}$		0.026	0.031		
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\ \text{V}$, $I_D = -8.4\ \text{A}$		20		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.7\ \text{A}$, $V_{GS} = 0\ \text{V}$		- 0.75	- 1.2	V	
Dynamic^b							
Total Gate Charge	Q_g	$V_{DS} = -10\ \text{V}$, $V_{GS} = -5\ \text{V}$, $I_D = -8.4\ \text{A}$		17	25	nC	
Gate-Source Charge	Q_{gs}			5			
Gate-Drain Charge	Q_{gd}			6.7			
Gate Resistance	R_g	$f = 1\ \text{MHz}$		2.4	12	18	Ω
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = -10\ \text{V}$, $R_L = 10\ \Omega$ $I_D \approx -1\ \text{A}$, $V_{GEN} = -10\ \text{V}$, $R_g = 6\ \Omega$		11	17	ns	
Rise Time	t_r			10	15		
Turn-Off Delay Time	$t_{d(\text{off})}$			94	140		
Fall Time	t_f			60	90		
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.7\ \text{A}$, $dl/dt = 100\ \text{A}/\mu\text{s}$		55	80		

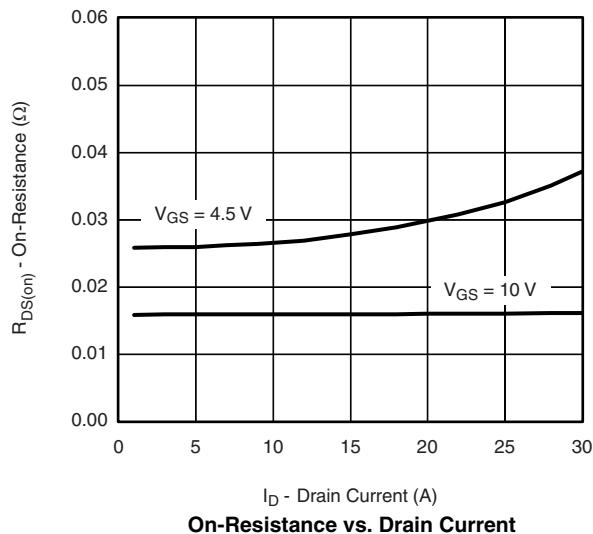
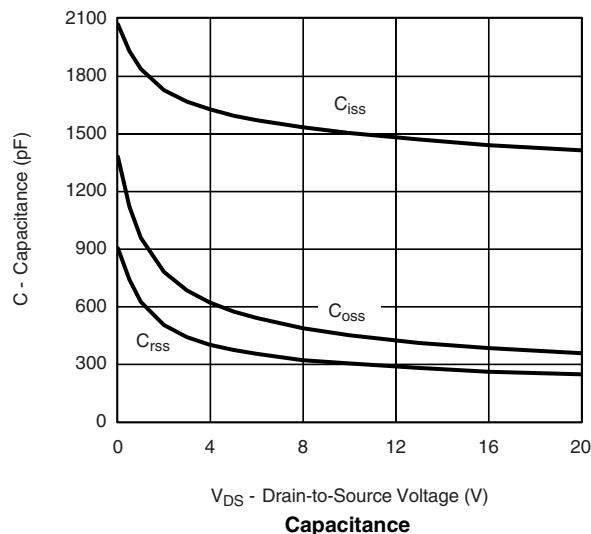
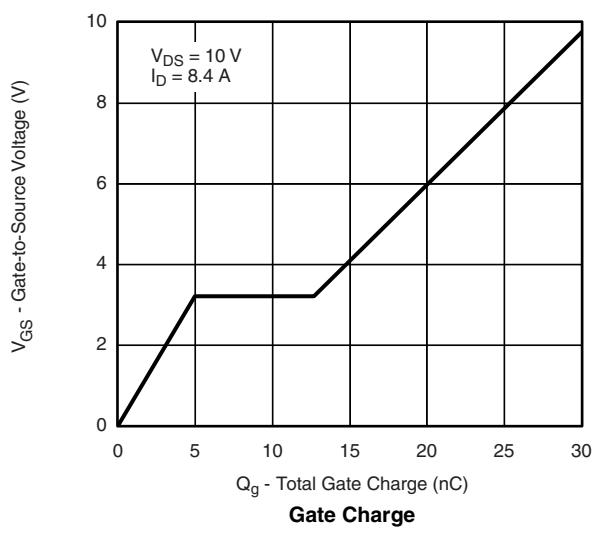
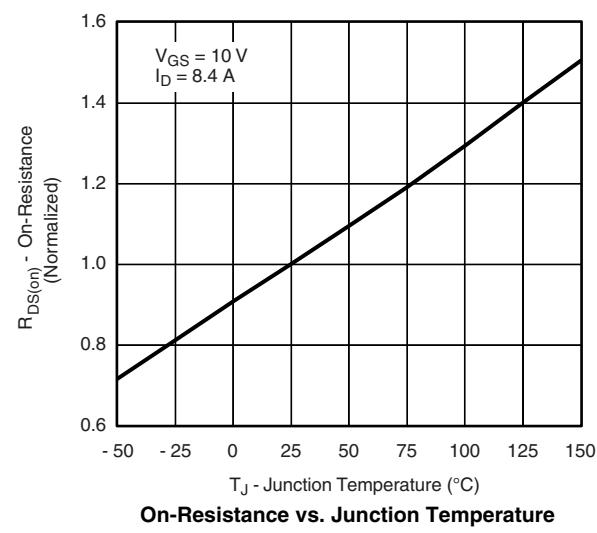
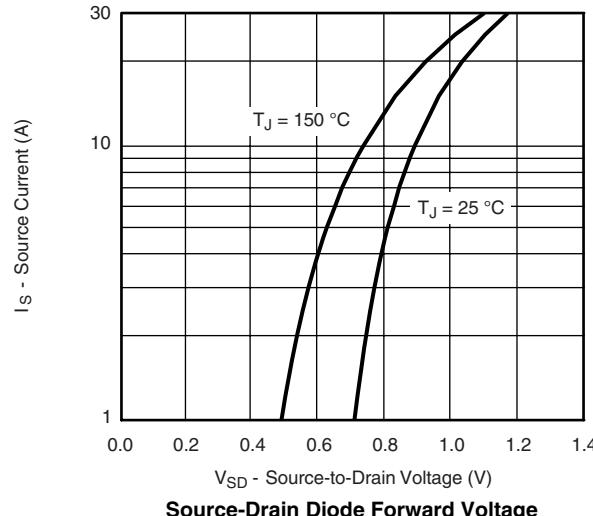
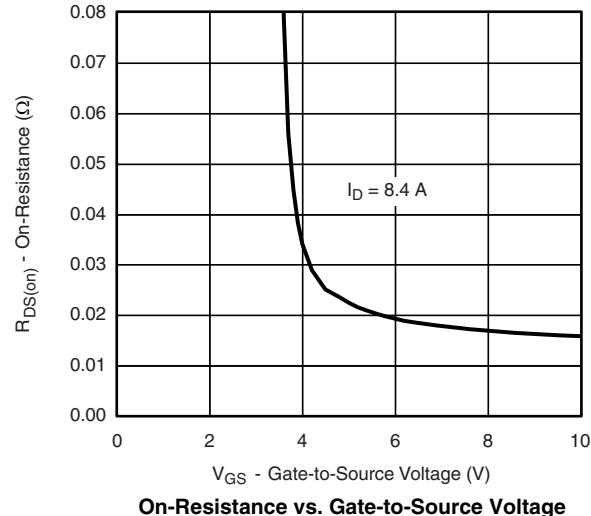
Notes:

a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\ %$.

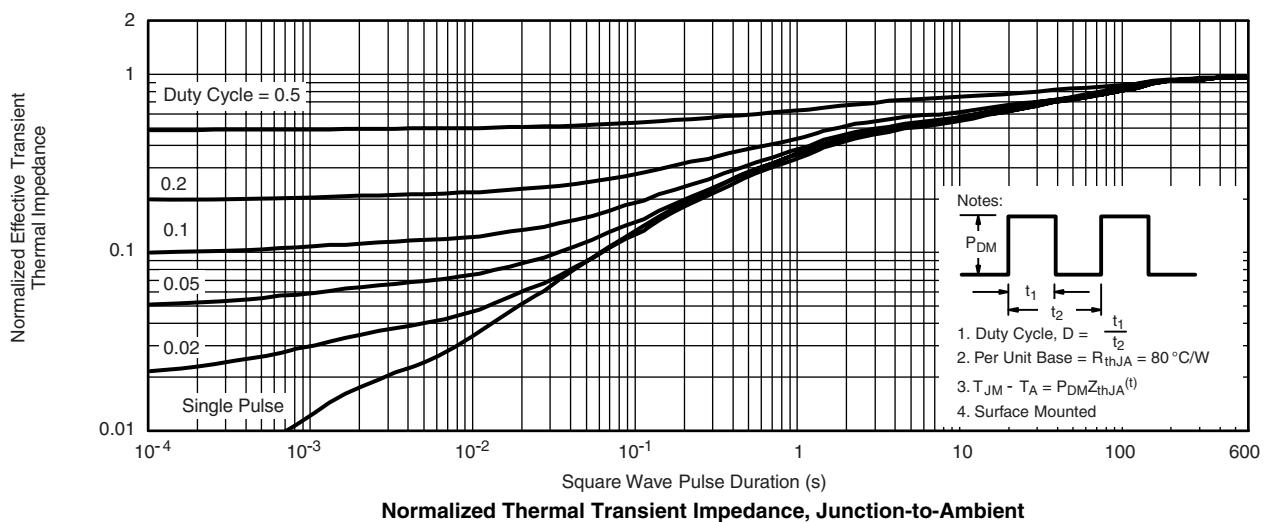
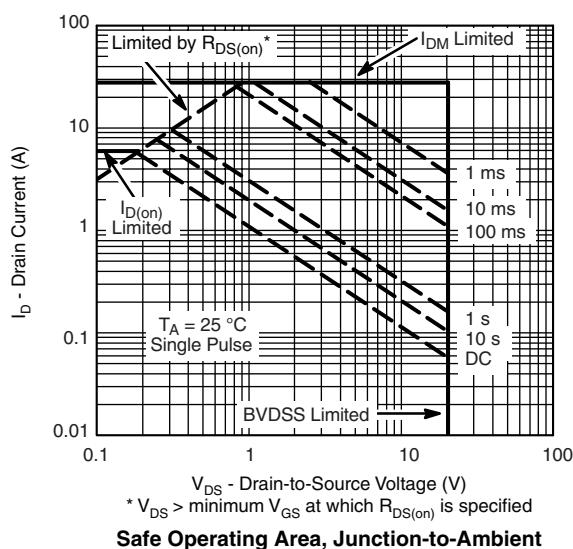
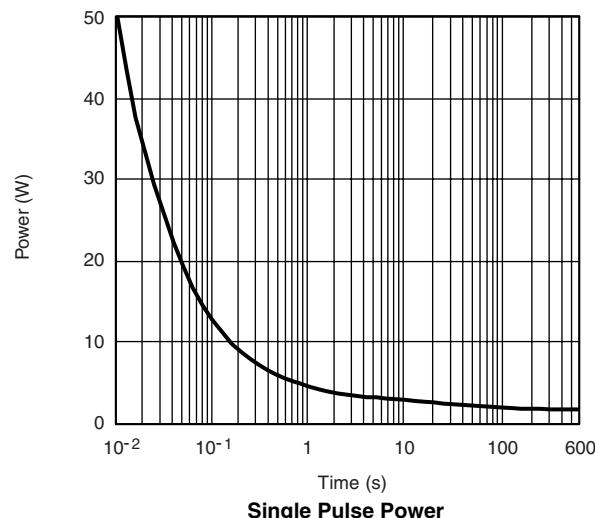
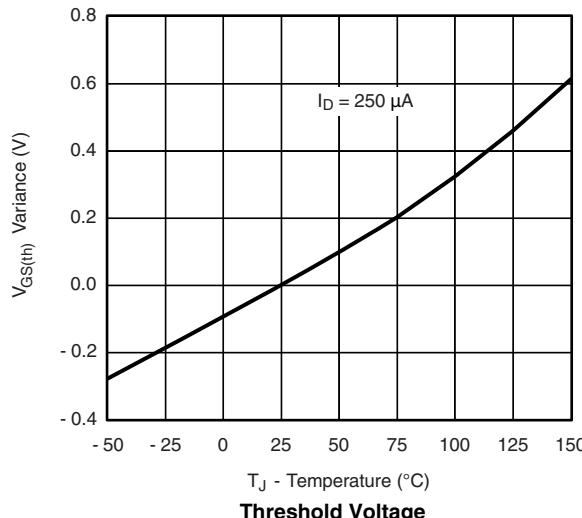
b. Guaranteed by design, not subject to production testing.

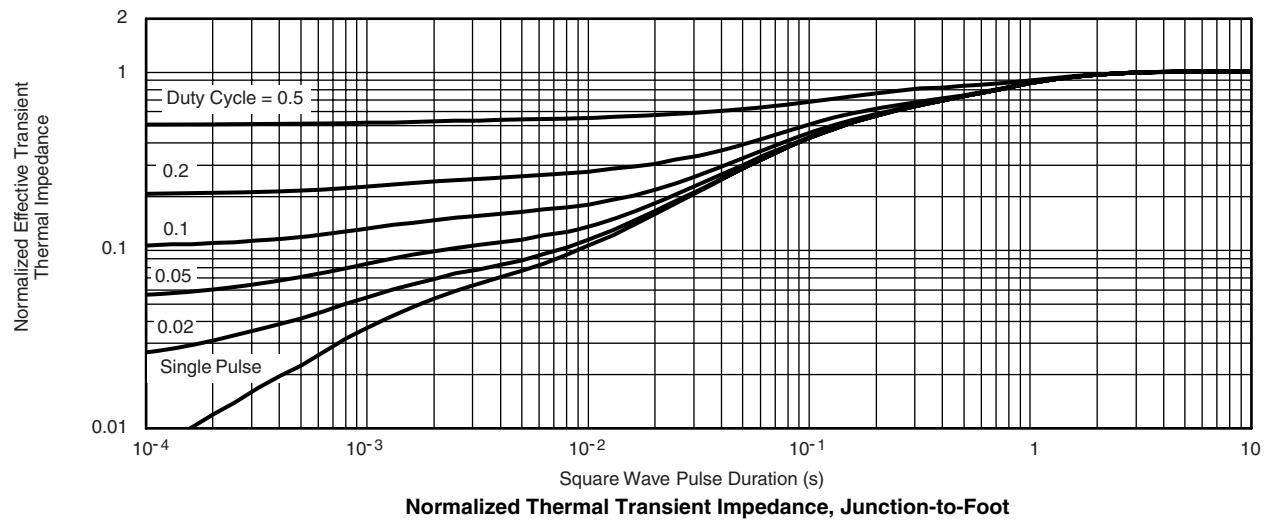
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25°C , unless otherwise noted

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On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

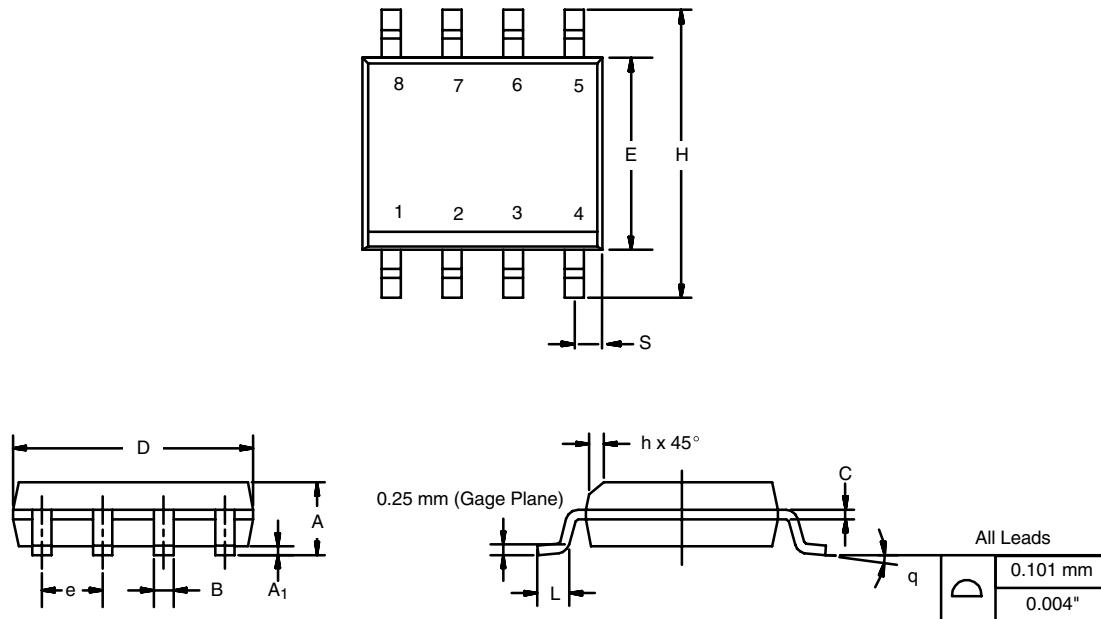


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


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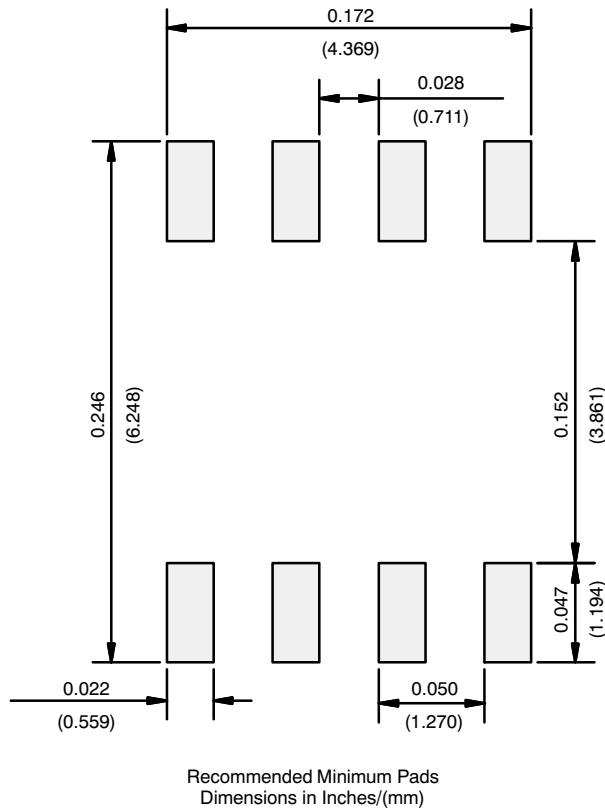
SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



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